

AMENDMENTS TO THE CLAIMS

The following listing of claims replaces all prior versions, and listings, of claims in the application:

1. (Currently amended) A light emitting heterostructure comprising:

a substrate;

a light generating structure formed over the substrate;

an electron blocking layer formed over the light generating structure, wherein the electron blocking layer allows light to pass therethrough;

a distributed semiconductor heterostructure Bragg reflector (DBR) structure formed over the ~~light generating structure~~ electron blocking layer; and

a p-type layer formed over the DBR structure.

2. (Canceled)

3. (Original) The heterostructure of claim 1, further comprising:

a buffer layer formed on the substrate; and

a second layer formed on the buffer layer, wherein the light generating structure is formed on the second layer.

4. (Original) The heterostructure of claim 3, further comprising a contact layer formed on the second layer.

5. (Original) The heterostructure of claim 1, further comprising a contact layer formed above the DBR structure.

6. (Original) The heterostructure of claim 5, further comprising a metal layer formed on the contact layer.

Claims 7-8 (Withdrawn)

9. (Original) The heterostructure of claim 1, further comprising a reflective layer formed over the DBR structure.

10. (Original) The heterostructure of claim 1, wherein the substrate comprises a transparent substrate.

11. (Currently amended) A light emitting device comprising:

a substrate;

an n-type layer formed over the substrate;

a light generating structure formed over the n-type layer;

an electron blocking layer formed over the light generating structure, wherein the electron blocking layer allows light to pass therethrough;

a distributed semiconductor heterostructure Bragg reflector (DBR) structure formed over the ~~light generating structure~~ electron blocking layer; and

a p-type layer formed over the DBR structure.

12. (Original) The device of claim 11, further comprising a reflective layer formed on the p-type layer.

13. (Currently amended) ~~The device of claim 12, further comprising~~ A light emitting device comprising:

a substrate;

an n-type layer formed over the substrate;

a light generating structure formed over the n-type layer;

a distributed semiconductor heterostructure Bragg reflector (DBR) structure formed over the light generating structure;

a p-type layer formed over the DBR structure;

a reflective layer formed on the p-type layer; and

a contact layer formed on the p-type layer, wherein the reflective layer and the contact layer form at least one of [:-] a set of alternating stripes [and] or a set of alternating squares.

14. (Original) The device of claim 11, further comprising:

a first contact formed on the n-type layer; and

a second contact formed above the p-type layer.

15. (Currently amended) The device of claim 11, wherein the device comprises at least one of []
a light emitting diode (LED), an ultraviolet LED, and or a laser.

16. (Currently amended) An ultraviolet light emitting heterostructure comprising:

an n-type layer;

a light generating structure formed over the n-type layer;

an electron blocking layer formed over the light generating structure, wherein the electron
blocking layer allows light to pass therethrough;

a distributed semiconductor heterostructure Bragg reflector (DBR) structure formed over
the ~~light generating structure~~ electron blocking layer; and

a p-type layer formed over the DBR structure.

Claims 17-20 (Withdrawn)

21. (Previously presented) The heterostructure of claim 16, further comprising a substrate,
wherein the n-type layer formed over the substrate.

22. (Previously presented) The heterostructure of claim 1, further comprising an n-type layer
formed over the substrate, wherein the light generating structure is formed over the n-type layer.

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